

MR3029-31/DIV
Appl. No. 10/697,308
Response to Office Action dated 24 March 2005

Amendments to the Claims:

This listing of Claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1 - 16 (canceled).

Claim 17 (currently amended): A structure of a LED device, the structure comprising:

a LED substrate having an uppermost layer; and
a transparent layer having Zn dopants therein on said uppermost layer of said LED substrate, wherein said transparent layer is composed of a semiconductor compound different to that of said uppermost layer -
~~comprises a metallic Zn dopant.~~

Claim 18 (original): The structure according to claim 17, wherein said transparent layer is formed by LPE process.

Claim 19 (original): The structure according to claim 17, wherein said transparent layer is formed by LPE process utilizing a supersaturated solution comprising metallic antimony (Sb) and indium (In) as a solvent.

Claim 20 (original): The structure according to claim 18, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of a solvent of a supersaturated solution in the LPE process.

Claim 21 (original): The structure according to claim 19, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of Sb of the supersaturated solution in the LPE process.

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Claim 22 (new): A structure of a LED device, the structure comprising:
a LED substrate having an uppermost GaP layer; and
an non-GaP transparent layer having Zn dopants therein on said
uppermost GaP layer formed by a LPE process using a supersaturated
solution.

Claim 23 (new): The structure according to claim 22, wherein said
non-GaP transparent layer is formed by LPE process utilizing a
supersaturated solution comprising metallic antimony (Sb) and indium (In)
as a solvent.

Claim 24 (new): The structure according to claim 22, wherein said Zn
dopant is in an amount of 1/1000 to 1/10 by weight of a solvent of a
supersaturated solution in the LPE process.

Claim 25 (new): The structure according to claim 22, wherein said Zn
dopant is in an amount of 1/1000 to 1/10 by weight of Sb of the
supersaturated solution in the LPE process.